

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:  
    peripheral electrodes formed on a periphery of a  
    semiconductor chip;  
    internal electrodes formed inside the peripheral electrodes  
    on the semiconductor chip; and  
    circuits formed in the semiconductor chip,  
    wherein the peripheral electrodes are connected to the  
    circuits by an internal line, and the internal electrodes are  
    connected to the circuits and the peripheral electrodes by the  
    internal line, and  
    wherein the same signal is either an input and/or output  
    either to or from both an internal electrode and peripheral  
electrode.

2. (Original) A semiconductor device according to Claim 1,  
    wherein the internal electrodes are smaller than the peripheral  
    electrodes.

3. (Original) A semiconductor device according to Claim 1,  
    wherein the internal electrodes comprise at least one selected  
    from the group consisting of a power supply terminal, a ground  
    terminal, and a clock terminal.

4. (Currently Amended) A semiconductor device according to Claim 1, wherein the peripheral electrodes not connected to the internal electrodes are used as terminals for RF high frequency signals.

5. (Original) A semiconductor device comprising:  
peripheral electrodes formed on a periphery of a semiconductor chip;  
internal electrodes formed inside the peripheral electrodes on the semiconductor chip; and  
circuits formed in the semiconductor chip,  
wherein the peripheral electrodes are connected to the circuits by an internal line, the internal electrodes are connected to the circuits and the peripheral electrodes by the internal line, and the internal electrodes are also connected to rewired lines, the rewired lines formed above the internal electrodes with an insulating layer therebetween, and at ends of the rewired lines formed area array electrodes.

6. (Original) A semiconductor device comprising:  
peripheral electrodes formed on a periphery of a semiconductor chip;

internal electrodes formed inside the peripheral electrodes on the semiconductor chip;

area array electrodes connected to selected one of the peripheral electrodes and the internal electrodes and formed on the semiconductor chip; and

circuits formed in the semiconductor chip,

wherein the peripheral electrodes are connected to the circuits by an internal line, the internal electrodes are connected to the circuits and the peripheral electrodes by the internal line, and the area array electrodes comprise first area array electrodes connected to the internal electrodes by rewired lines and second area array electrodes connected to the peripheral electrodes by rewired lines.

7. (Original) A semiconductor device according to Claim 6, wherein the first area array electrodes comprise at least one selected from the group consisting of a power supply terminal, a ground terminal, and a clock terminal.

8. (Currently Amended) A semiconductor device according to Claim 6, wherein the second area array electrodes are used as terminals for RF high frequency signals.